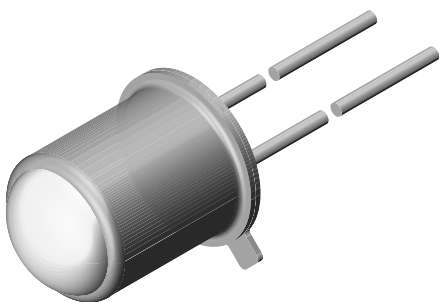




## Infrared Emitting Diode, 950 nm, GaAlAs, MQW



### FEATURES

- Package type: leaded
- Package form: TO-18
- Dimensions (in mm):  $\varnothing$  4.7
- Peak wavelength:  $\lambda_p = 950$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\varphi = \pm 4^\circ$
- Low forward voltage
- Good spectral matching with Si photodetectors
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT

### DESCRIPTION

TSTS7100 is an infrared, 950 nm emitting diode in GaAlAs multi quantum well (MQW) technology in a hermetically sealed TO-18 package with lens.

### APPLICATIONS

- Radiation source in near infrared range

### PRODUCT SUMMARY

| COMPONENT | $I_e$ (mW/sr) | $\varphi$ (°) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-----------|---------------|---------------|------------------|------------|
| TSTS7100  | 105           | $\pm 4$       | 950              | 15         |

#### Note

- Test conditions see table “Basic Characteristics”

### ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM |
|---------------|-----------|------------------------------|--------------|
| TSTS7100      | Bulk      | MOQ: 1000 pcs, 1000 pcs/bulk | TO-18        |

#### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER                              | TEST CONDITION               | SYMBOL     | VALUE       | UNIT             |
|----------------------------------------|------------------------------|------------|-------------|------------------|
| Reverse voltage                        |                              | $V_R$      | 5           | V                |
| Forward current                        |                              | $I_F$      | 100         | mA               |
| Power dissipation                      |                              | $P_V$      | 170         | mW               |
| Junction temperature                   |                              | $T_j$      | 125         | $^\circ\text{C}$ |
| Ambient temperature range              |                              | $T_{amb}$  | -40 to +85  | $^\circ\text{C}$ |
| Storage temperature range              |                              | $T_{stg}$  | -40 to +110 | $^\circ\text{C}$ |
| Soldering temperature                  | $t \leq 5$ s, 2 mm from case | $T_{sd}$   | 260         | $^\circ\text{C}$ |
| Thermal resistance junction to ambient | J-STD-051                    | $R_{thJA}$ | 500         | K/W              |

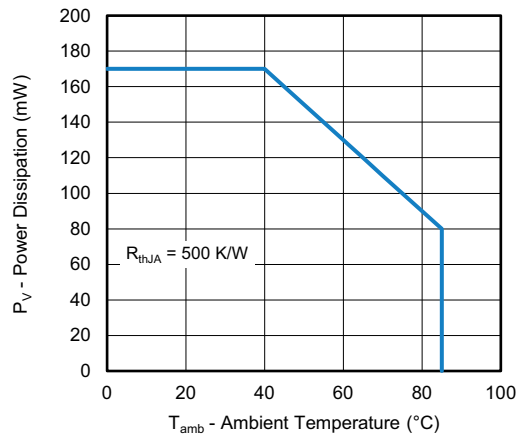


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

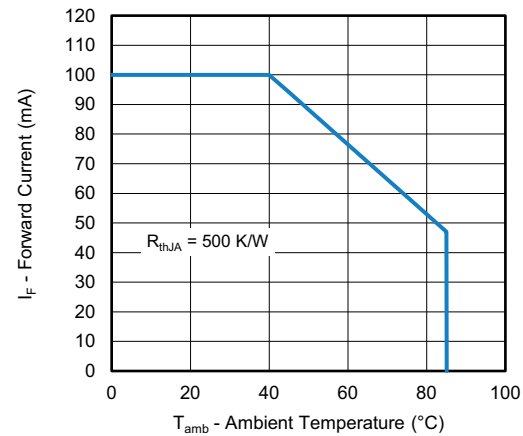


Fig. 2 - Forward Current Limit vs. Ambient Temperature

**BASIC CHARACTERISTICS** ( $T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified)

| PARAMETER                              | TEST CONDITION                                                   | SYMBOL           | MIN.                               | TYP.    | MAX. | UNIT          |
|----------------------------------------|------------------------------------------------------------------|------------------|------------------------------------|---------|------|---------------|
| Forward voltage                        | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $V_F$            | -                                  | 1.4     | 1.7  | V             |
|                                        | $I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$              | $V_F$            | -                                  | 2.2     | -    | V             |
| Temperature coefficient of $V_F$       | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $TK_{V_F}$       | -                                  | -1.1    | -    | mV/K          |
| Reverse current                        |                                                                  | $I_R$            | Not designed for reverse operation |         |      | $\mu\text{A}$ |
| Junction capacitance                   | $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0\text{ mW/cm}^2$ | $C_j$            | -                                  | 56      | -    | pF            |
| Radiant intensity                      | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $I_e$            | 65                                 | 105     | 185  | mW/sr         |
| Radiant power                          | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $\phi_e$         | -                                  | 17      | -    | mW            |
| Temperature coefficient of $\phi_e$    | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $TK_{\phi_e}$    | -                                  | -0.5    | -    | %/K           |
| Angle of half intensity                |                                                                  | $\phi$           | -                                  | $\pm 4$ | -    | $^{\circ}$    |
| Peak wavelength                        | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $\lambda_p$      | -                                  | 950     | -    | nm            |
| Spectral bandwidth                     |                                                                  | $\Delta\lambda$  | -                                  | 30      | -    | nm            |
| Temperature coefficient of $\lambda_p$ | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $TK_{\lambda_p}$ | -                                  | 0.2     | -    | %/K           |
| Rise time                              | $I_F = 100\text{ mA}$                                            | $t_r$            | -                                  | 15      | -    | ns            |
| Fall time                              | $I_F = 100\text{ mA}$                                            | $t_f$            | -                                  | 15      | -    | ns            |

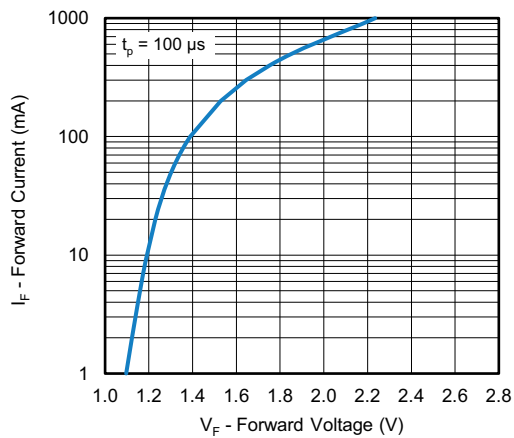
**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

Fig. 3 - Forward Current vs. Forward Voltage

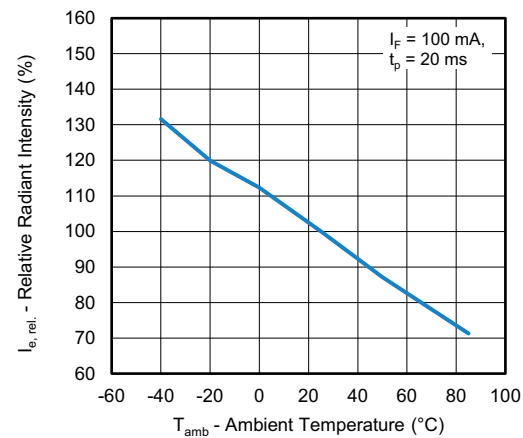


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

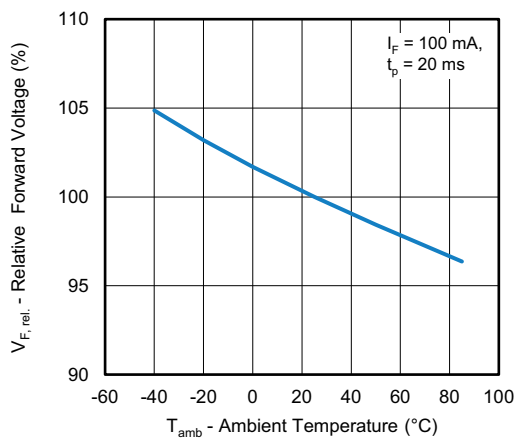


Fig. 4 - Forward Voltage vs. Ambient Temperature

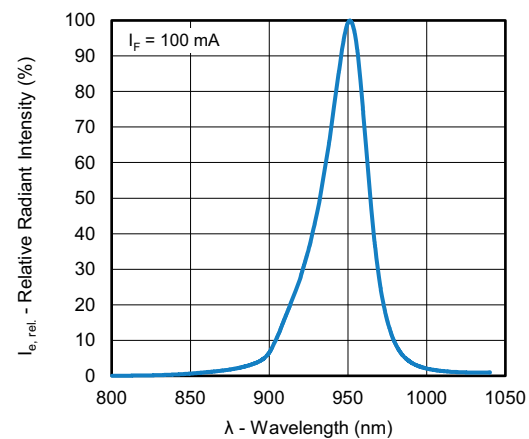


Fig. 7 - Relative Radiant Intensity vs. Wavelength

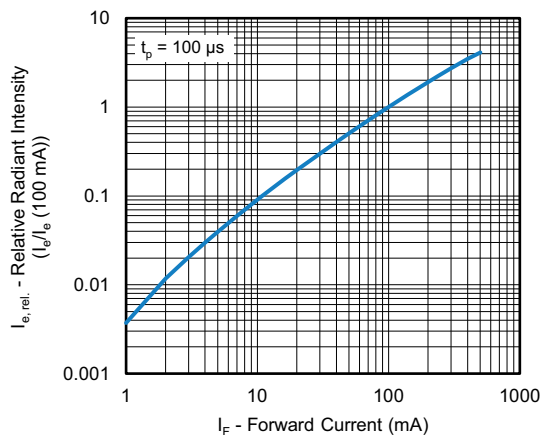


Fig. 5 - Relative Radiant Intensity vs. Forward Current

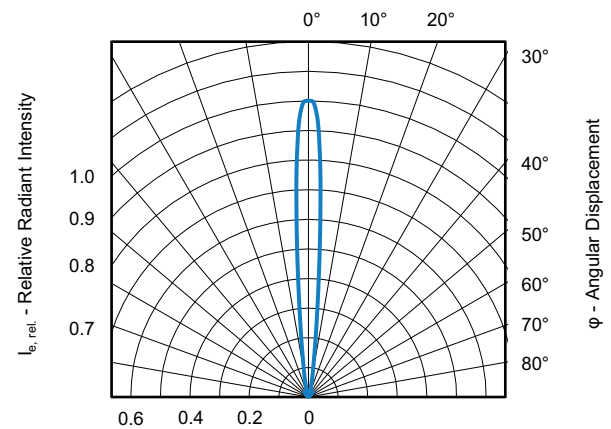
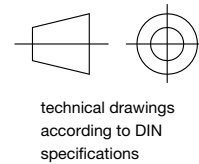
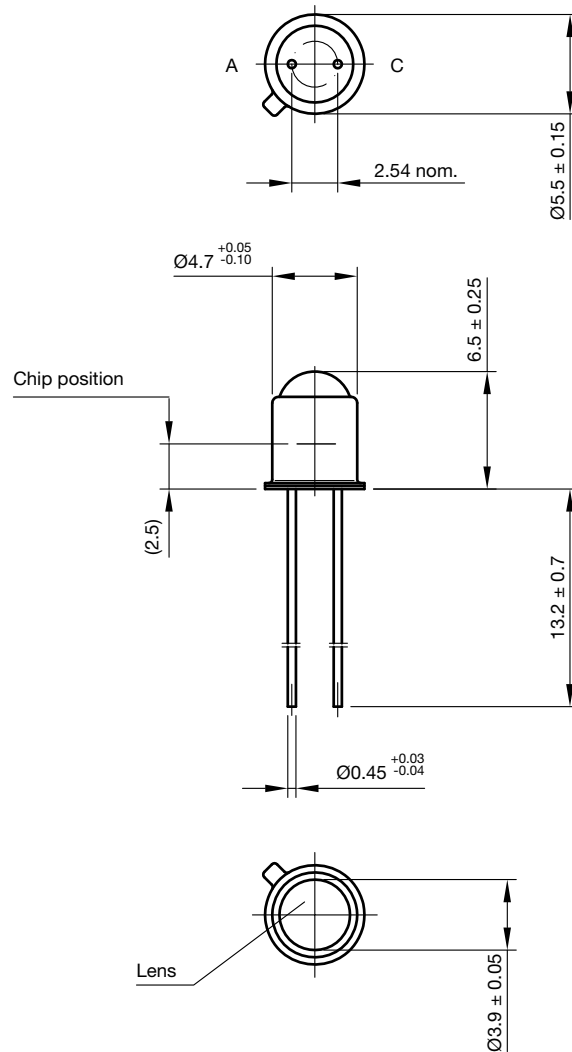


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



**PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.503-5002.02-4  
Issue: 2VK; 25.03.2024



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